

REMARKS

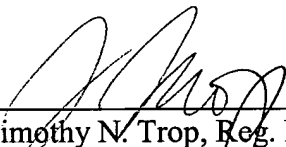
It is submitted that the term "epitaxially deposited" refers to forming an epitaxial layer by deposition while the term in its well-accepted meaning means forming a layer by growing. This conclusion is supported only by the Applicants' own application at page 5. At that page, it is suggested that an epitaxial silicon layer may be grown. However, it is also indicated that an epitaxial boron doped silicon may be selectively deposited.

It seems to be a distinction without a difference. As explained in the attached article from Semiconductor Fabtech, silicon epitaxy consists of atom-by-atom deposition with layer growth resulting from a chemical reaction between the silicon source gas and the free silicon surface at elevated temperatures. Thus, it seems that silicon epitaxy, whether it is called growth or deposition, involves both growth and deposition. In any case, it is clear that those skilled in the art contemplate silicon epitaxy to involve deposition.

Therefore, reconsideration of the rejection of the claim is respectfully requested.

Respectfully submitted,

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